

# Abstracts

## A High Power Density and High Efficiency UHF-Band HFET for Low Voltage Operation

---

*T. Kunii, Y. Kohno, T. Kitano, S. Miyakuni, J. Udomoto, K. Yamamoto, K. Maemura, H. Takano, O. Ishihara and N. Tsubouchi. "A High Power Density and High Efficiency UHF-Band HFET for Low Voltage Operation." 1995 MTT-S International Microwave Symposium Digest 95.2 (1995 Vol. II [MWSYM]): 575-578.*

A high power density and high efficiency AlGaAs/GaAs Heterostructure FET (HFET) for 0.9GHz Digital Cellular Phone Systems has been successfully developed. The device has delivered a high power density of 117mW/mm with a power-added efficiency (PAE) of 37.6% with a low adjacent channel power (ACP) of -53.4dBc at a low drain bias of 3.3V at 950 MHz operating frequency.

[Return to main document.](#)